

## **HAT2058R**

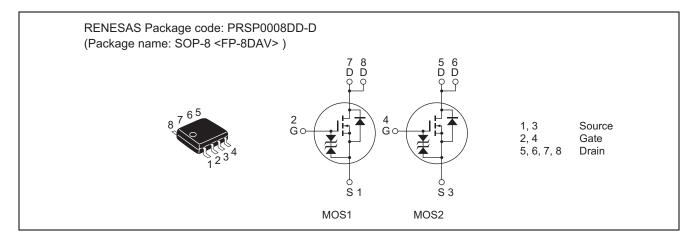
# Silicon N Channel Power MOS FET High Speed Power Switching

REJ03G1174-0300 Rev.3.00 Aug 25, 2009

### **Features**

- Low on-resistance
- Capable of 4 V gate drive
- · Low drive current
- High density mounting
- "J" is for Automotive application High temperature D-S leakage guarantee Avalanche rating

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	100	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub> Note 2	4	Α
Drain peak current	I <sub>D (pulse)</sub> Note 1	32	Α
Body-drain diode reverse drain current	I <sub>DR</sub>	4	Α
Avalanche current	I <sub>AP</sub> Note 4	_	Α
Avalanche energy	E <sub>AR</sub> Note 4	_	mJ
Channel dissipation	Pch Note 2	2	W
	Pch Note 3	3	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. 1 Drive operation: When using the glass epoxy board (FR4  $40 \times 40 \times 1.6$  mm), PW  $\leq 10$  s
- 3. 2 Drive operation: When using the glass epoxy board (FR4  $40 \times 40 \times 1.6$  mm), PW  $\leq 10$  s
- 4. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$

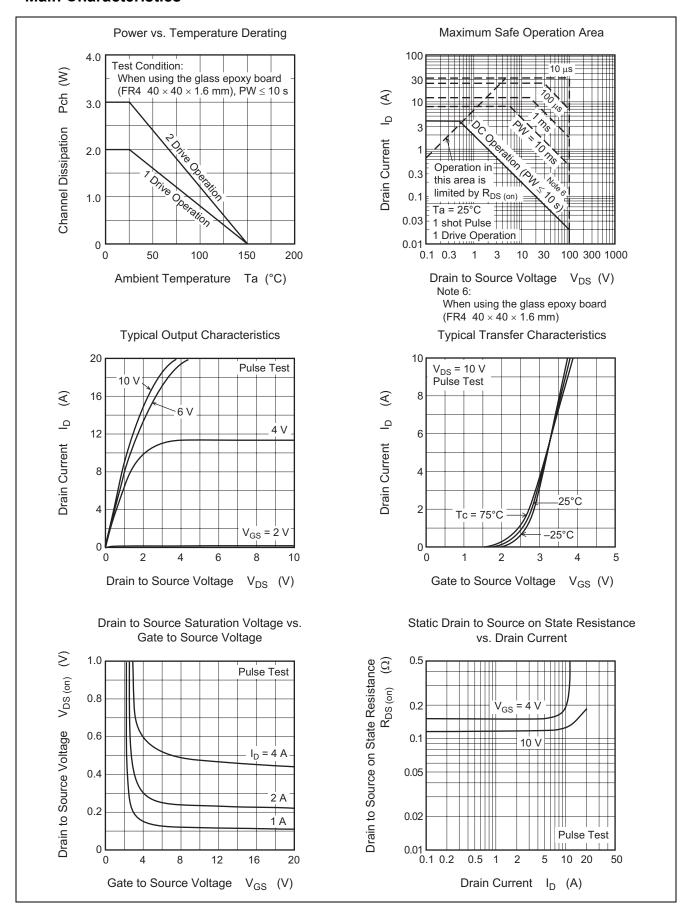
### **Electrical Characteristics**

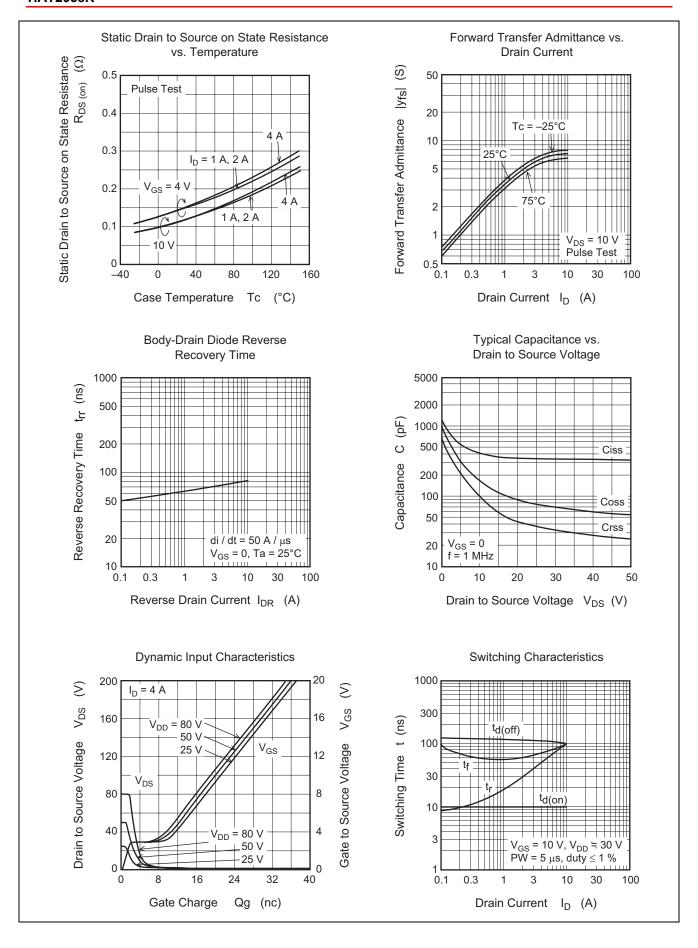
 $(Ta = 25^{\circ}C)$ 

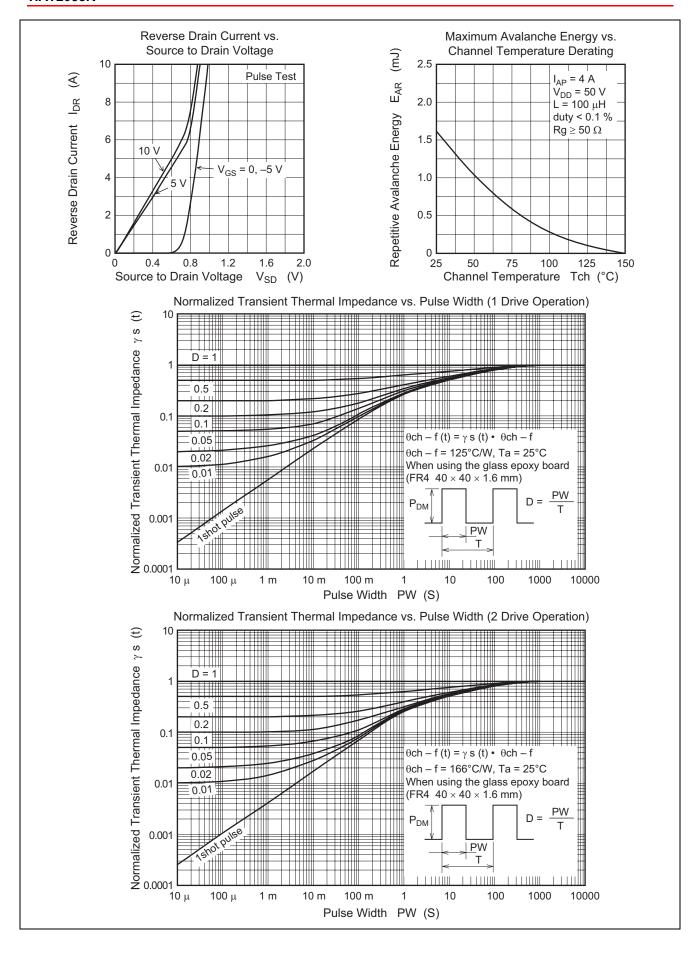
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR) DSS</sub>	100	_	_	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR) GSS</sub>	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μА	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS (off)</sub>	1.0	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y <sub>fs</sub>	3	5	_	S	$I_D = 2 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note 5}}$
Static drain to source on state resistance	R <sub>DS (on)</sub>	_	120	145	mΩ	$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 5}}$
	R <sub>DS (on)</sub>	_	150	180	mΩ	$I_D = 2 \text{ A}, V_{GS} = 4 \text{ V}^{\text{Note 5}}$
Input capacitance	Ciss	_	420	_	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0
Output capacitance	Coss	_	180	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	100	_	pF	
Turn-on delay time	t <sub>d (on)</sub>	_	10	_	ns	$V_{GS} = 10 \text{ V}, I_D = 2 \text{ A},$
Rise time	t <sub>r</sub>	_	30	_	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	t <sub>d (off)</sub>	_	110	_	ns	
Fall time	t <sub>f</sub>	_	60	_	ns	
Body-drain diode forward voltage	$V_{DF}$	_	0.85	1.1	V	$I_F = 4 \text{ A}, V_{GS} = 0^{\text{Note 5}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	75	_	ns	I <sub>F</sub> = 4 A, V <sub>GS</sub> = 0
						di <sub>F</sub> /dt = 50 A/μs

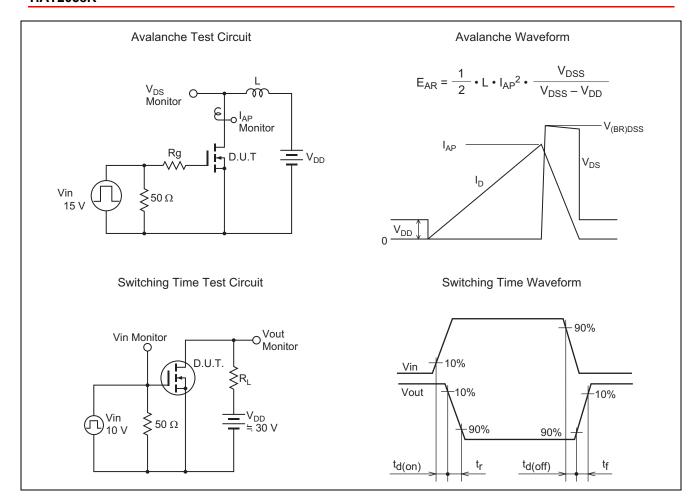
Note: 5. Pulse test

### **Main Characteristics**

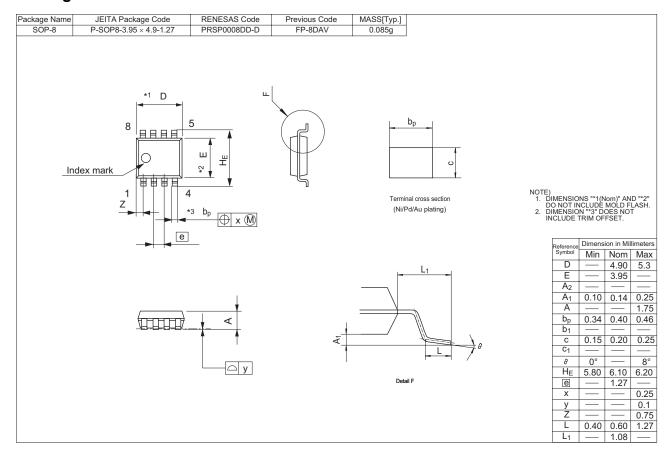








### **Package Dimensions**



### **Ordering Information**

Part Name	Quantity	Shipping Container
HAT2058R-EL-E	2500 pcs	Taping

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

  1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect to the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

  3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is such as the development of the dev



### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510